



KOREAN PATENT ABSTRACTS

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(54) METHOD FOR FABRICATING CAPACITOR OF SEMICONDUCTOR DEVICE TO PREVENT PATTERN FROM COLLAPSING

(57) Abstract:

PURPOSE: A method for fabricating a capacitor of a semiconductor device is provided to prevent a pattern from collapsing by increasing the surface area between edge patterns which is an interface between a cell area and a peripheral circuit area of the semiconductor device.

CONSTITUTION: A lower insulation layer with a predetermined underlying structure is formed on a semiconductor substrate. A storage node contact hole is formed which exposes the semiconductor substrate through the lower insulation layer. A conductive layer for a storage node(20) is formed which is connected to the semiconductor substrate through the storage node contact hole. The storage node is formed by a photolithography process using a storage node mask in which a storage node of a quadrilateral structure is rotated at an angle of -80 to 80 degrees.

